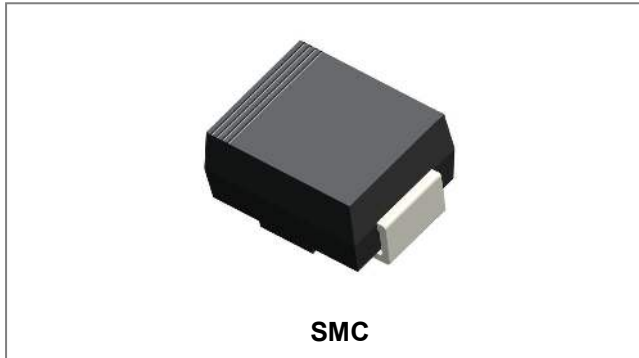


30BQ200 SCHOTTKY RECTIFIER



Features

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	200	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L=148^\circ\text{C}$, rectangular wave form	3.0	A
		50% duty cycle @ $T_L=138^\circ\text{C}$, rectangular wave form	4.0	
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine pulse, $T_C=25^\circ\text{C}$	55	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 3 A, Pulse, $T_J = 25^\circ\text{C}$	0.83	0.92	V
	V_{F2}	@ 3 A, Pulse, $T_J = 75^\circ\text{C}$	-	0.76	V
Reverse Current*	I_{R1}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 25^\circ\text{C}$	0.00003	1	mA
	I_{R2}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 100^\circ\text{C}$	0.006	3	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	50	60	pF
Series Inductance	L_S	Measured lead to lead 5 mm from package body	3.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

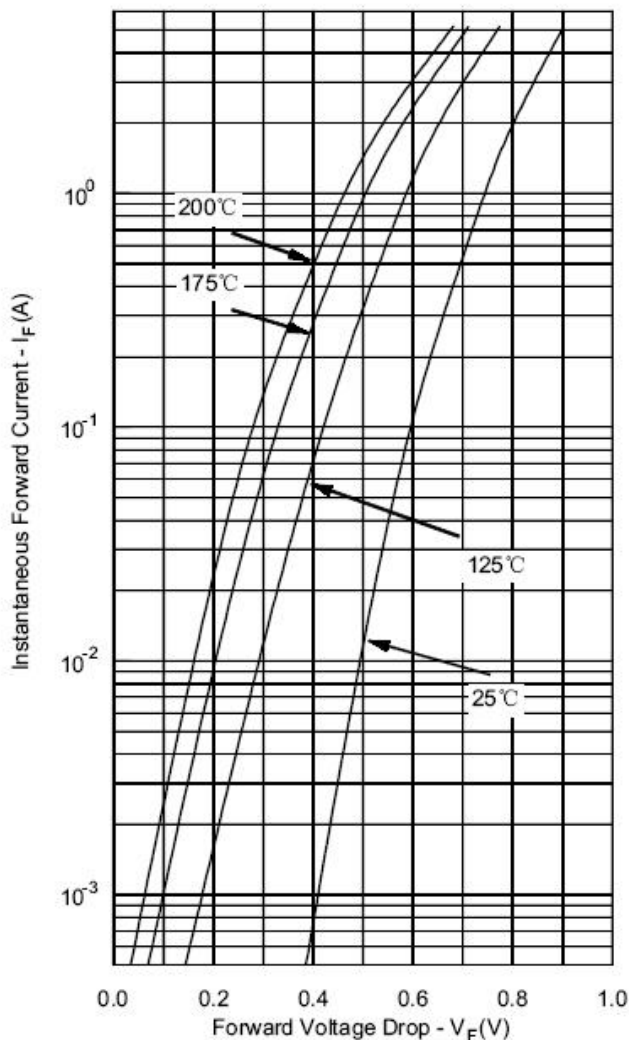
* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

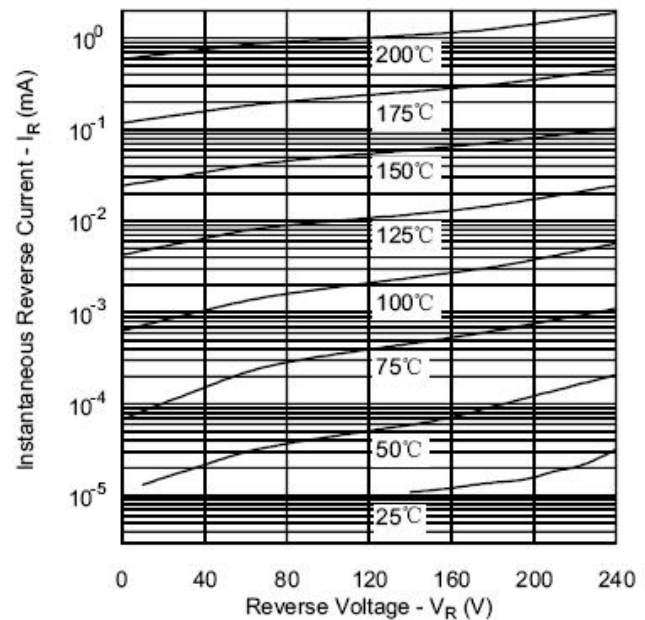
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T_{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Lead	$R_{\theta JL}$	-	12	°C/W
Typical Thermal Resistance Junction to Case	$R_{\theta JA}$	DC operation	46	°C/W
Approximate Weight	wt	-	0.21	g
Case Style	SMC			

Ratings and Characteristics Curves

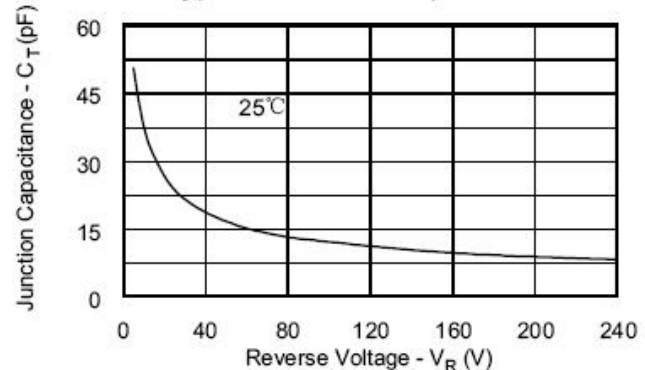
Typical Forward Characteristics



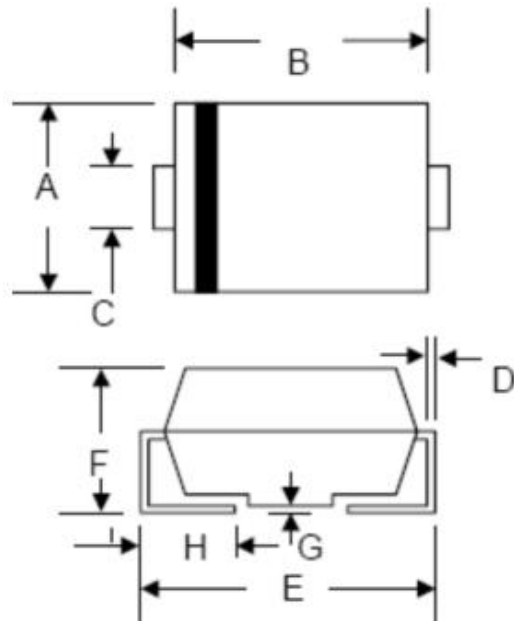
Typical Reverse Characteristics



Typical Junction Capacitance



Mechanical Dimensions SMC




SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	5.59	6.22	0.220	0.245
B	6.60	7.11	0.260	0.280
C	2.75	3.25	0.108	0.128
D	0.152	0.305	0.006	0.012
E	7.75	8.25	0.305	0.325
F	2.00	2.95	0.079	0.116
G	0.051	0.203	0.002	0.008
H	0.76	1.60	0.030	0.063

Ordering Information

Device	Package	Shipping
30BQ200	SMC (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

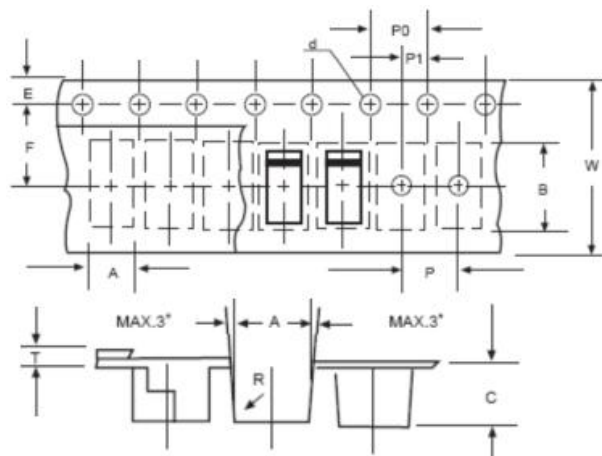


Where XXXXX is YYWWL

SC3N = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Eooxv resin UL:94V-0

Carrier Tape Specification SMC



SYMBOL	Millimeters	
	Min.	Max.
A	5.90	6.10
B	8.20	8.40
C	2.40	2.60
d	1.40	1.60
E	1.40	1.60
F	7.60	7.70
P	7.90	8.10
P0	3.90	4.10
P1	3.90	4.10
T	-	0.600
W	15.80	16.20

Technical Data
Data Sheet N0026, Rev. A



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